



## DOCUMENT CHANGE REQUEST

DCR number 517 Changes required for: General

Date: 2009/05/06

Date sent: 2009/05/06

Originator: S Jeffery - ESCC

Organisation: ESA/ESTEC

Status: IMPLEMENTED

Title: Transistors Silicon Switching PNP, based on type 2N3467

Number: 5208/009

Issue: 2

Other documents affected:

Page:

See attachment

Paragraph:

See attachment

Original wording:

Proposed wording:

Update the Maximum Ratings table (see the attachment for details) so that this detail spec is clear, complete and the content and format is in-line with other detail specifications for similar Part Types.

Justification:

Improve the content and clarity of the spec.

Attachments:

5208009\_Issue\_3\_-\_Draft\_A.pdf, null

Modifications:

N/A

Approval signature:

Date signed:

2009-05-06



Pages 1 to 13

## TRANSISTORS, SWITCHING, PNP

BASED ON TYPE 2N3467

ESCC Detail Specification No. 5208/009

as applicable

Issue 3 - Draft A	<del>October 2008</del>
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Document Custodian: European Space Agency - see <https://escies.org>



as applicable

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**DOCUMENTATION CHANGE NOTICE**

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DCR No.	CHANGE DESCRIPTION
● <del>388</del>	Specification up issued to incorporate editorial and technical changes per DCR.

t6d

At  $T_{case} \leq +25^{\circ}C$

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	$V_{CBO}$	-40	V	Over entire operating temperature range
Collector-Emitter Voltage	$V_{CEO}$	-40	V	
Emitter-Base Voltage	$V_{EBO}$	-5	V	
Collector Current	$I_C$	-1	A	Continuous
Power Dissipation	$P_{tot1}$	1	W	At $T_{amb} \leq +25^{\circ}C$
	$P_{tot2}$	5	W	Note 1
Operating Temperature Range	$T_{op}$	-65 to +200	$^{\circ}C$	Note 1
Storage Temperature Range	$T_{stg}$	-65 to +200	$^{\circ}C$	Note 1
Soldering Temperature	$T_{sol}$	+265	$^{\circ}C$	Note 2

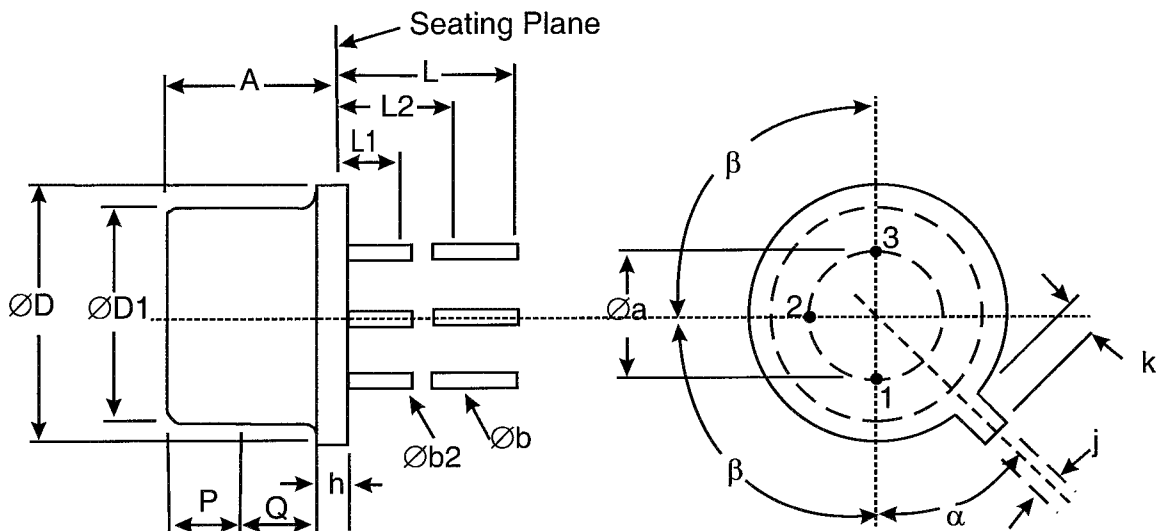
see attached

**NOTES:**

1. For  $T_{amb} > +25^{\circ}C$ , derate linearly to 0W at  $+200^{\circ}C$
1. For Variants with tin-lead plating or hot solder dip lead finish all testing performed at  $T_{amb} > +125^{\circ}C$  shall be carried out in a 100% inert atmosphere.
2. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 Metal Can Package (TO-39) - 3 lead



Symbols	Dimensions mm		Notes
	Min	Max	
Øa	4.83	5.35	
A	6	6.6	
Øb	0.4	0.533	2, 3
Øb2	0.4	0.483	2, 3

Thermal Resistance, Junction-to-Ambient	$R_{th(j-a)}$	175	°C/W	
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	30	°C/W	